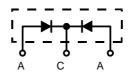
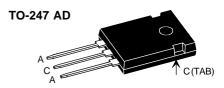


HiPerFRED™ Epitaxial Diode with common cathode and soft recovery

 $I_{FAV} = 2x15 A$ $V_{RRM} = 400 V$ $t_{rr} = 30 ns$

V _{RSM}	V _{RRM}	Туре
400	400	DSEC 30-04A





A = Anode, C = Cathode, TAB = Cathode

Symbol	Conditions	Maximum Ratings	
I _{FRMS}	T _c = 145°C; rectangular, d = 0.5	50 15	A A
I _{FSM}	$T_{VJ} = 45^{\circ}C$; $t_p = 10 \text{ ms (50 Hz), sine}$	tbd	A
E _{AS}	$T_{VJ} = 25$ °C; non-repetitive $I_{AS} = \text{tbd A}$; $L = \text{tbd } \mu\text{H}$	tbd	mJ
I _{AR}	$V_A = 1.5 \cdot V_R \text{ typ.}; f = 10 \text{ kHz}; \text{ repetitive}$	tbd	A
T _{VJ} T _{VJM} T _{stg}		-55+175 175 -55+150	°C °C °C
$\overline{P_{tot}}$	T _C = 25°C	95	W
M _d	mounting torque	0.81.2	Nm
Weight	typical	6	g

Symbol	Conditions	Characteristic Values		
		typ.	max.	
I _R ①	$T_{VJ} = 25^{\circ}\text{C};$ $V_{R} = V_{RRM}$ $T_{VJ} = 150^{\circ}\text{C};$ $V_{R} = V_{RRM}$		100 0.5	μA mA
V _F ②	$I_F = 15 \text{ A};$ $T_{VJ} = 150 ^{\circ}\text{C}$ $T_{VJ} = 25 ^{\circ}\text{C}$		1.06 1.47	V
R _{thJC}		0.25	1.6	K/W K/W
t _{rr}	$I_F = 1 \text{ A}$; -di/dt = 100 A/ μ s; $V_R = 30 \text{ V}$; $T_{VJ} = 25^{\circ}\text{C}$	30		ns
I _{RM}	$V_R = 100 \text{ V}; \ I_F = 25 \text{ A}; -di_F/dt = 100 \text{ A}/\mu\text{s}$ $T_{VJ} = 100 ^{\circ}\text{C}$	5.0	6.3	Α

Features

- · International standard package
- · Planar passivated chips
- Very short recovery time
- · Extremely low switching losses
- Low I_{RM}-values
- · Soft recovery behaviour
- Epoxy meets UL 94V-0

Applications

- Antiparallel diode for high frequency switching devices
- · Antisaturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- · Inductive heating
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

Advantages

- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{RM} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Dimensions see pages IXYS Data Book

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %

@ Pulse Width = 300 $\mu s,$ Duty Cycle < 2.0 %

Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, test conditions and dimensions.
